



1N582x

## LOW DROP POWER SCHOTTKY RECTIFIER

## MAIN PRODUCTS CHARACTERISTICS

I <sub>F(AV)</sub>	3 A
V <sub>RRM</sub>	40 V
T <sub>j</sub>	150°C
V <sub>F</sub> (max)	0.475 V

## FEATURES AND BENEFITS

- VERY SMALL CONDUCTION LOSSES
- NEGLIGIBLE SWITCHING LOSSES
- EXTREMELY FAST SWITCHING
- LOW FORWARD VOLTAGE DROP
- AVALANCHE CAPABILITY SPECIFIED

## DESCRIPTION

Axial Power Schottky rectifier suited for Switch Mode Power Supplies and high frequency DC to DC converters. Packaged in DO-201AD these devices are intended for use in low voltage, high frequency inverters, free wheeling, polarity protection and small battery chargers.

## ABSOLUTE RATINGS (limiting values)



Symbol	Parameter	Value			Unit	
		1N5820	1N5821	1N5822		
V <sub>RRM</sub>	Repetitive peak reverse voltage	20	30	40	V	
I <sub>F(RMS)</sub>	RMS forward current	10			A	
I <sub>F(AV)</sub>	Average forward current	T <sub>L</sub> = 100°C δ = 0.5		3	A	
		T <sub>L</sub> = 110°C δ = 0.5	3	3	A	
I <sub>FSM</sub>	Surge non repetitive forward current	tp = 10 ms Sinusoidal	80			A
P <sub>ARM</sub>	Repetitive peak avalanche power	tp = 1μs T <sub>j</sub> = 25°C	1700			W
T <sub>stg</sub>	Storage temperature range	- 65 to + 150			°C	
T <sub>j</sub>	Maximum operating junction temperature *	150			°C	
dV/dt	Critical rate of rise of reverse voltage	10000			V/μs	

\* :  $\frac{dP_{tot}}{dT_j} < \frac{1}{R_{th}(j-a)}$  thermal runaway condition for a diode on its own heatsink

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### THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
R <sub>th</sub> (j-a)	Junction to ambient	Lead length = 10 mm	80	°C/W
R <sub>th</sub> (j-l)	Junction to lead	Lead length = 10 mm	25	°C/W

### STATIC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Tests Conditions		1N5820	1N5821	1N5822	Unit
I <sub>R</sub> *	Reverse leakage current	T <sub>j</sub> = 25°C	V <sub>R</sub> = V <sub>RRM</sub>	2	2	2	mA
		T <sub>j</sub> = 100°C		20	20	20	mA
V <sub>F</sub> *	Forward voltage drop	T <sub>j</sub> = 25°C	I <sub>F</sub> = 3 A	0.475	0.5	0.525	V
		T <sub>j</sub> = 25°C	I <sub>F</sub> = 9.4 A	0.85	0.9	0.95	V

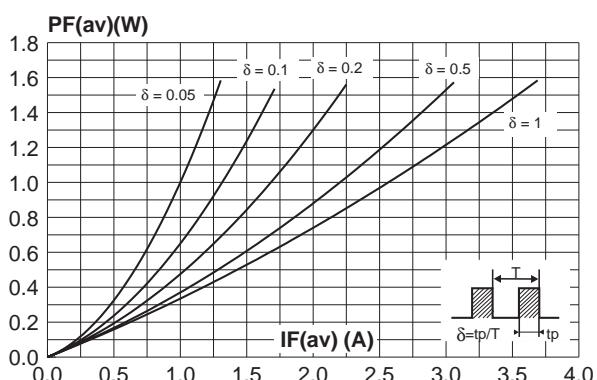
Pulse test : \* tp = 380 µs, δ < 2%

To evaluate the conduction losses use the following equations :

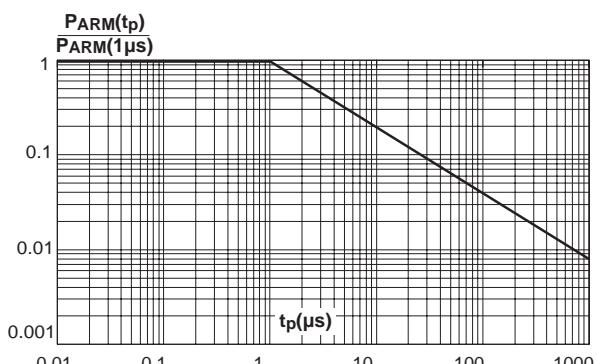
$$P = 0.33 \times I_{F(AV)} + 0.035 I_{F(RMS)}^2 \text{ for 1N5820 / 1N5821}$$

$$P = 0.33 \times I_{F(AV)} + 0.060 I_{F(RMS)}^2 \text{ for 1N5822}$$

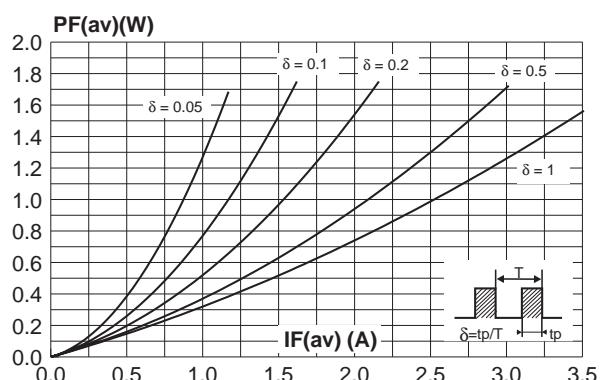
**Fig. 1:** Average forward power dissipation versus average forward current (1N5820/1N5821).



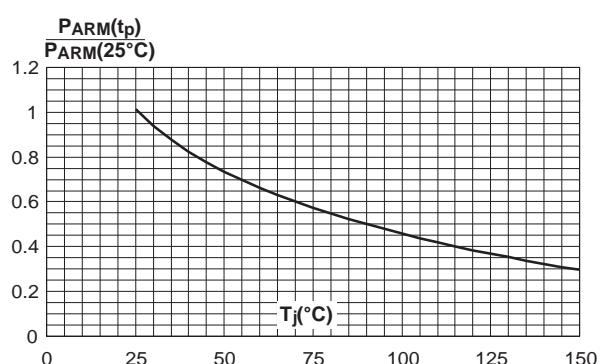
**Fig. 3:** Normalized avalanche power derating versus pulse duration.



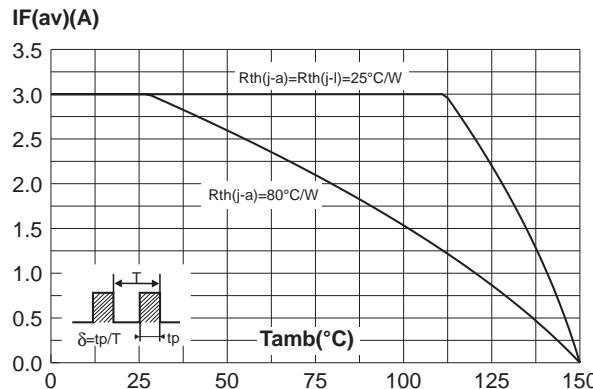
**Fig. 2:** Average forward power dissipation versus average forward current (1N5822).



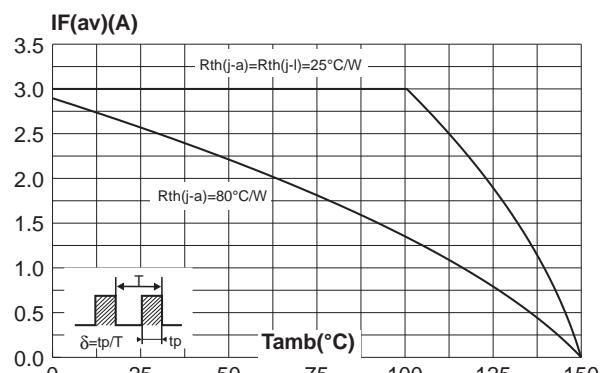
**Fig. 4:** Normalized avalanche power derating versus junction temperature.



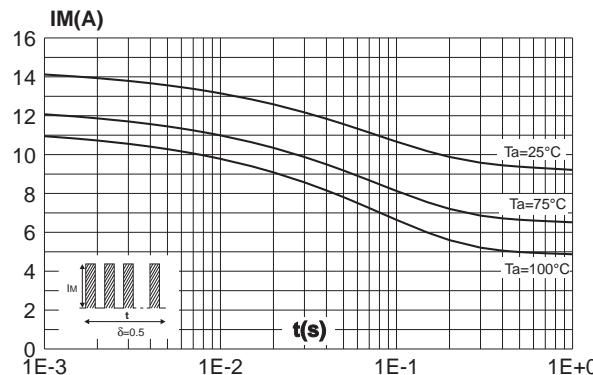
**Fig. 5-1:** Average forward current versus ambient temperature ( $\delta=0.5$ ) (1N5820/1N5821).



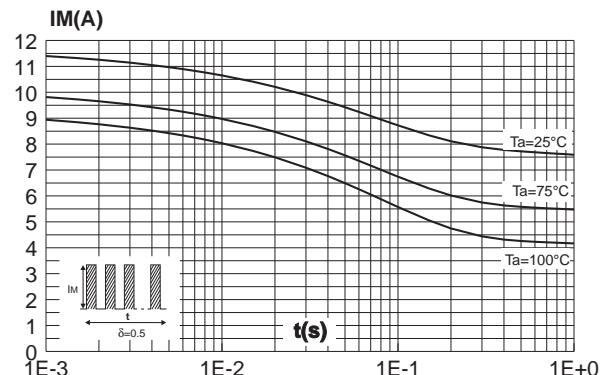
**Fig. 5-2:** Average forward current versus ambient temperature ( $\delta=0.5$ ) (1N5822).



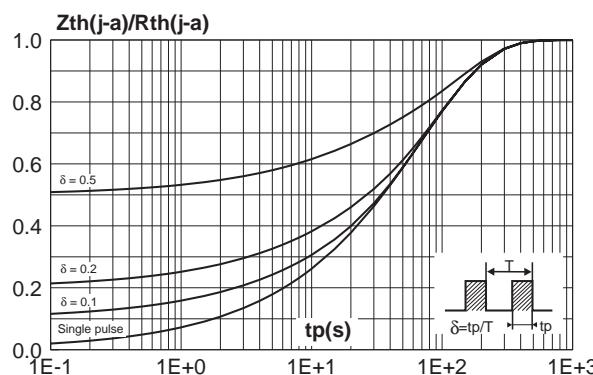
**Fig. 6-1:** Non repetitive surge peak forward current versus overload duration (maximum values) (1N5820/1N5821).



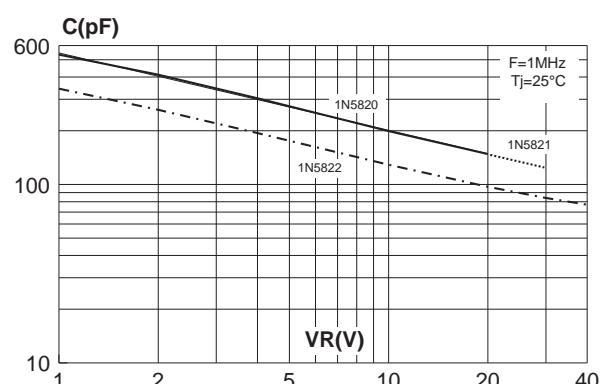
**Fig. 6-2:** Non repetitive surge peak forward current versus overload duration (maximum values) (1N5822).



**Fig. 7:** Relative variation of thermal impedance junction to ambient versus pulse duration (epoxy printed circuit board,  $e(\text{Cu})=35\text{mm}$ , recommended pad layout).



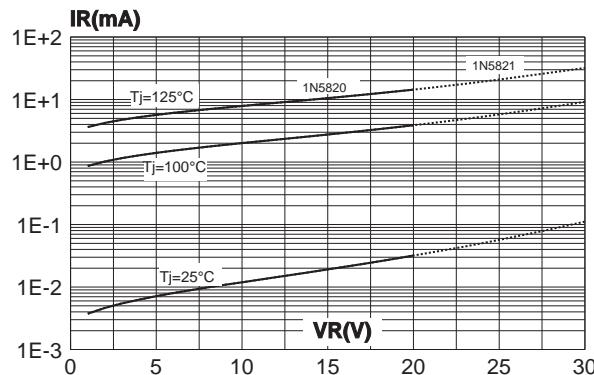
**Fig. 8:** Junction capacitance versus reverse voltage applied (typical values).



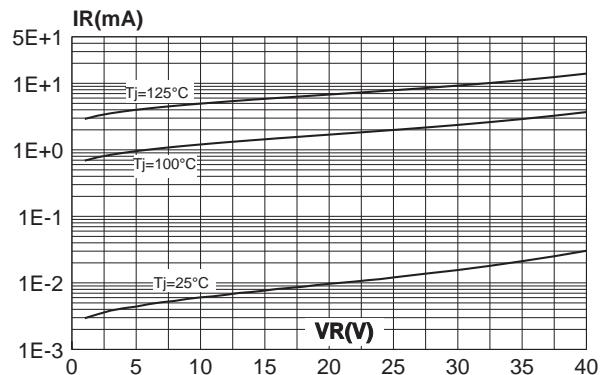
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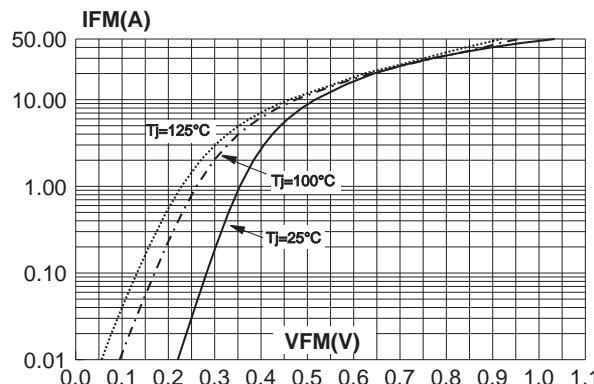
**Fig. 9-1:** Reverse leakage current versus reverse voltage applied (typical values) (1N5820/1N5821).



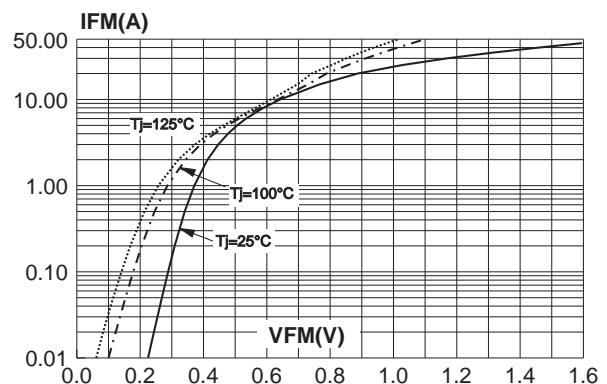
**Fig. 9-2:** Reverse leakage current versus reverse voltage applied (typical values) (1N5822).



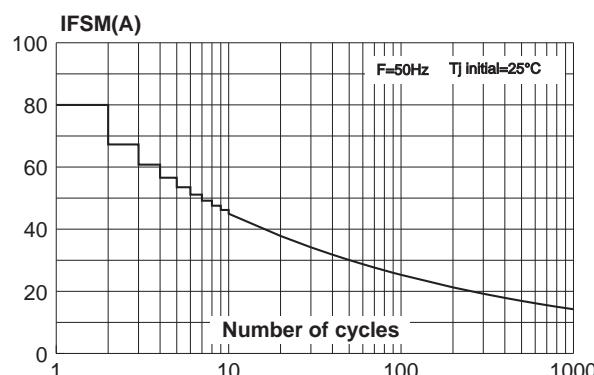
**Fig. 10-1:** Forward voltage drop versus forward current (typical values) (1N5820/1N5821).



**Fig. 10-2:** Forward voltage drop versus forward current (typical values) (1N5822).

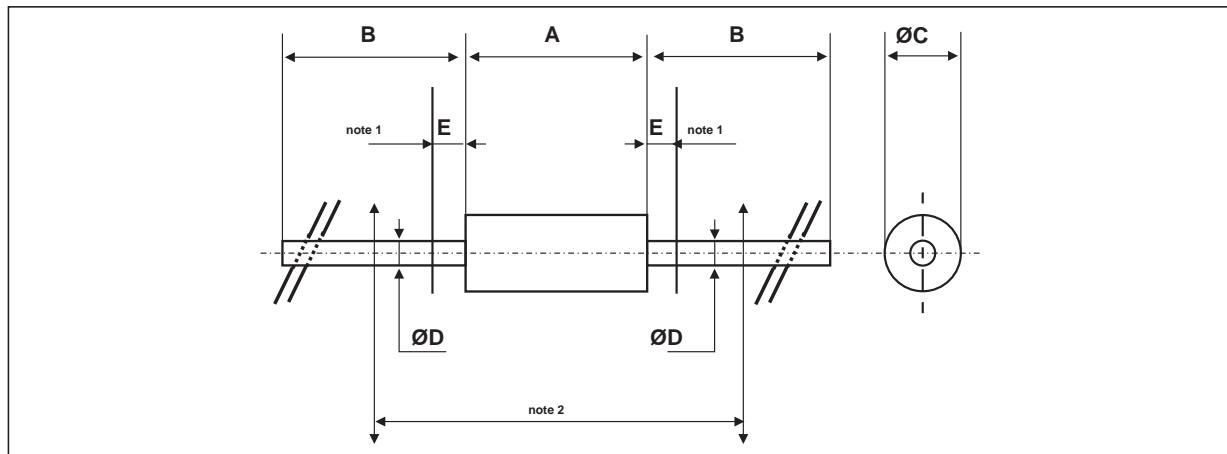


**Fig. 11:** Non repetitive surge peak forward current versus number of cycles.



## PACKAGE MECHANICAL DATA

DO-201AD plastic



REF.	DIMENSIONS				NOTES	
	Millimeters		Inches			
	Min.	Max.	Min.	Max.		
A		9.50		0.374	1 - The lead diameter $\blacktriangleleft$ D is not controlled over zone E	
B	25.40		1.000		2 - The minimum axial length within which the device may be placed with its leads bent at right angles is 0.59"(15 mm)	
$\blacktriangleleft$ C		5.30		0.209		
$\blacktriangleleft$ D		1.30		0.051		
E		1.25		0.049		

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
1N582x	Part number cathode ring	DO-201AD	1.12g	600	Ammopack
1N582xRL	Part number cathode ring	DO-201AD	1.12g	1900	Tape & reel

- EPOXY MEETS UL94,V0

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